

## CDBV6-54T/AD/CD/SD/BR-G

**Forward Current: 0.2A**  
**Reverse Voltage: 30V**  
**RoHS Device**

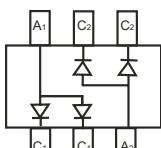
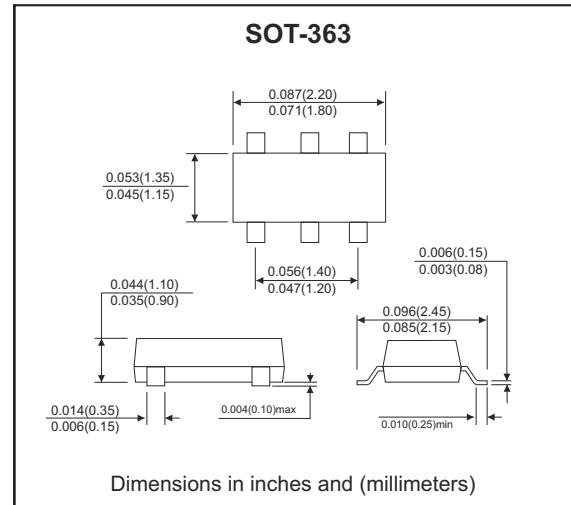


### Features

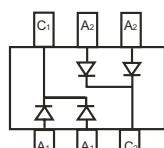
- Low forward voltage drop.
- Fast switching.
- Ultra-small surface mount package.
- PN junction guard ring for transient and ESD protection.
- Available in lead Free version.

### Mechanical data

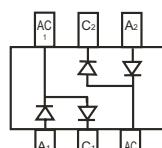
- Case: SOT-363, Molded Plastic
- Case material: UL 94V-0 flammability retardant classification.
- Terminals: Solderable per MIL-STD-202, Method 208
- Marking: Orientation: See diagrams below
- Weight: 0.006 grams (approx.)
- Marking: See diagrams below



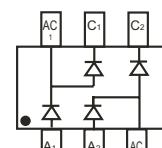
CDBV6-54AD-G\*  
Marking: KL6



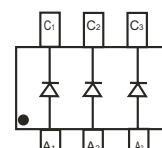
CDBV6-54CD-G\*  
Marking: KL7



CDBV6-54SD-G\*  
Marking: KL8



CDBV6-54BR-G  
Marking: KLB



CDBV6-54T-G  
Marking: KLA

\*Symmetrical configuration, no orientation indicator.

### Maximum Ratings (at Ta=25°C unless otherwise noted)

Parameter	Symbol	Limits		Unit
Peak repetitive reverse voltage Working peak reverse voltage DC blocking voltage	$V_{RRM}$ $V_{RWM}$ $V_R$	30		V
Forward continuous current (Note 1)	$I_F$	200		mA
Repetitive peak forward current (Note 1)	$I_{FRM}$	300		mA
Forward surge current (Note 1) @t<1.0s	$I_{FSM}$	600		mA
Power dissipation (Note 1)	$P_D$	200		mW
Thermal resistance, junction to ambient air (Note 1)	$R_{\theta JA}$	625		°C/W
Operation and storage temperature range	$T_J, T_{STG}$	-65 ~ +125		°C

### Electrical Characteristics (at Ta=25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Typ	Max	Unit
Reverse breakdown voltage (Note 2)	$I_R=100\mu A$	$V_{(BR)R}$	30			V
Forward voltage	$I_F=0.1mA$ $I_F=1mA$ $I_F=10mA$ $I_F=30mA$ $I_F=100mA$	$V_F$			240 320 400 500 1000	mV
Reverse leakage current (Note 2)	$V_R=25V$	$I_R$			2	μA
Total capacitance	$V_R=1.0V, f=1.0MHz$	$C_T$			10	pF
Reverse recovery time	$I_F=I_R=10mA$ to $I_R=1.0mA$ , $R_L=100\Omega$	$trr$			5	nS

Notes:

1. Device mounted on FR-4 PCB, 1×0.85×0.062 inch.
2. Short duration test pulse used to minimize self-heating effect.

# SMD Schottky Barrier Diode Arrays

**Comchip**  
SMD Diode Specialist

## ELECTRICAL CHARACTERISTIC CURVES (CDBV6-54T/AD/CD/SD/BR-G)

Fig.1 Forward Characteristics

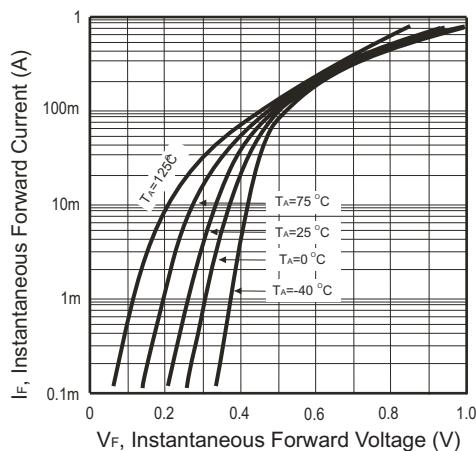


Fig.2 Reverse Characteristics

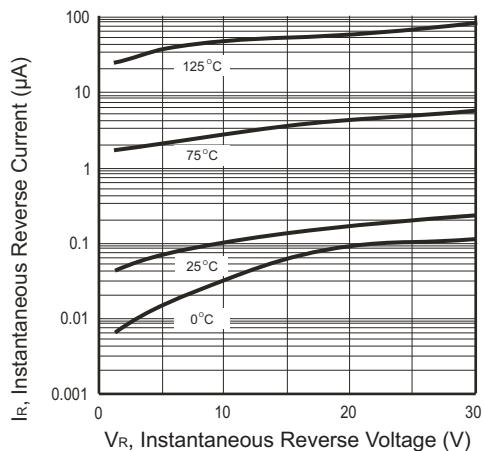


Fig.3 Capacitance Between Terminals Characteristics

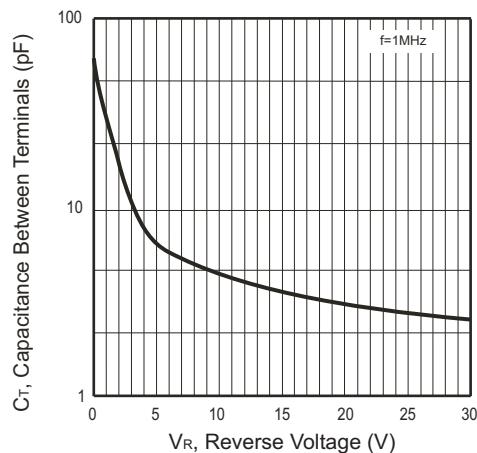


Fig.4 Power Derating Curve

